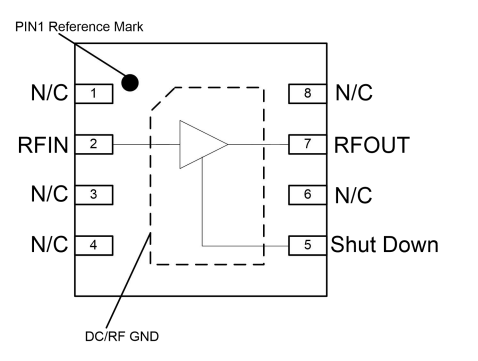


High Linearity Low Noise Gain Amplifier , 50 - 4200 MHz

Product Introduction

GHLN-9047 -DF2-8 is a 50MHz~4200MHz ultra-wideband, high linearity, low noise gain block amplifier. This amplifier can meet the needs of a variety of application scenarios, including small base stations, walkie-talkies, LTE/WCDMA communication systems and other wireless communication systems. GHLN-9047 -DF2-8 adopts the standard DFN2X2 label package. The amplifier integrates shutdown bias capability and all pins are equipped with ESD protection. The product quality level is changed to industrial grade.

| Block Diagram | Product Features |
|---|--|
|  <p style="text-align: center;">Bottom view</p> | <p>Working frequency: 50-4200MHz Noise figure: 1.5dB@1900MHz Small signal gain: 15.5dB@1900 MHz Gain flatness: 13.5±1.3dB from 2000 to 5000MHz P-1dB : 21dBm OIP3 : 39dBm Integrated shutdown function 50Ohm input and output +5V/65mA 2x2 mm 8 Pin DFN plastic package</p> |

Electrical performance parameters (TA = +25°C, Vd = +5V, 50Ω system)

| Index | Test Conditions | Minimum | Typical Value | Maximum | Unit |
|----------------------|--|---------|---------------|---------|------|
| Frequency Range | | 50 | | 4200 | MHz |
| Test frequency | | | 1900 | | MHz |
| Small Signal Gain | | | 15.5 | | dB |
| Input return loss | | | 11.5 | | dB |
| Output return loss | | | 13.5 | | dB |
| P-1 | | | 21 | | dBm |
| OIP3 | Pout=+4dBm/tone , Δf =1MHz | | 39 | | dBm |
| Noise Figure * | Without de-embedding, the estimated evaluation board loss is 0.15dB@1.9G | | 1.5 | | dB |
| Switching speed | Rise Time (10%-90%) | | 170 | | ns |
| | Fall Time (90%-10%) | | 260 | | ns |
| Shutdown control | On state | 0 | | 0.5 | V |
| | Off state (Power down) | +1.4 | +3.3 | VDD | V |
| Current | On state | | 65 | | mA |
| | Off state (Power down) | | 3 | | mA |
| Shutdown pin current | VPD ≥ 3V | | 250 | | uA |
| Thermal resistance | Channel to case | | | 65 | °C/W |

*Noise figure is the test data without de -embedding .

High Linearity Low Noise Gain Amplifier , 50 - 4200 MHz

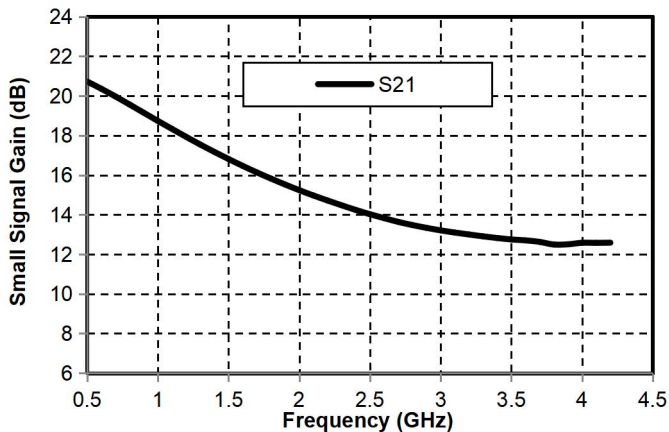
500M-5G electrical performance parameters

Electrical performance parameters ($T_A = +25^\circ\text{C}$, $V_d = +5\text{V}$, 50Ω system)

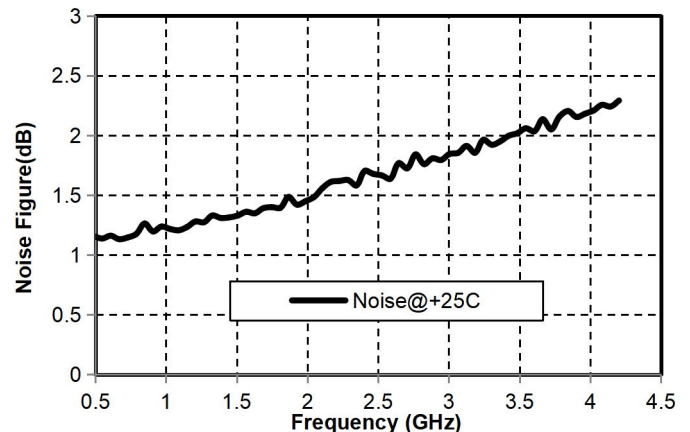
| Index | Test Conditions | Typical Value | | | | | Unit |
|--------------------|--|---------------|------|------|------|------|------|
| | | 900 | 1900 | 2700 | 3500 | 5000 | |
| Test frequency | | 900 | 1900 | 2700 | 3500 | 5000 | MHz |
| Small Signal Gain | | 19 | 15.5 | 13.5 | 12.5 | 12.5 | dB |
| Input return loss | | 13.5 | 11.5 | 11 | 11 | 10.5 | dB |
| Output return loss | | 14.5 | 13.5 | 11.5 | 10.5 | 11 | dB |
| P-1 | | 21 | 21 | 21 | 20.5 | 16.5 | dBm |
| OIP3 | Pout=+4 dBm /tone , $\Delta f = 1\text{MHz}$ | 37 | 36 | 36.5 | 35.5 | 33.5 | dBm |
| Noise Figure * | | 1.2 | 1.45 | 1.7 | 2.0 | 2.4 | dB |

*Noise figure is the test data without de -embedding .

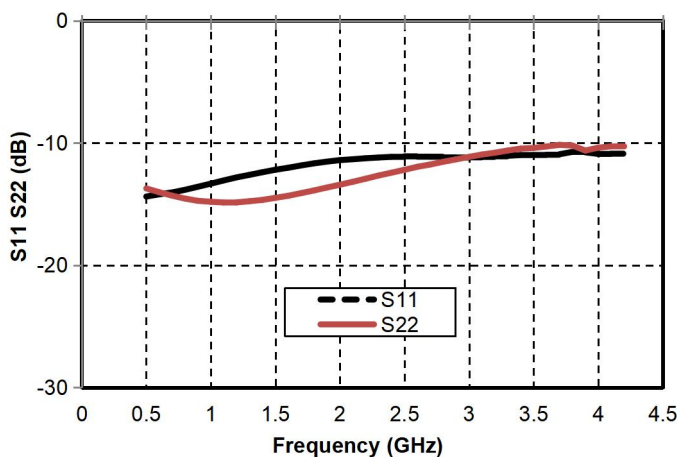
Small Signal Gain vs. Frequency



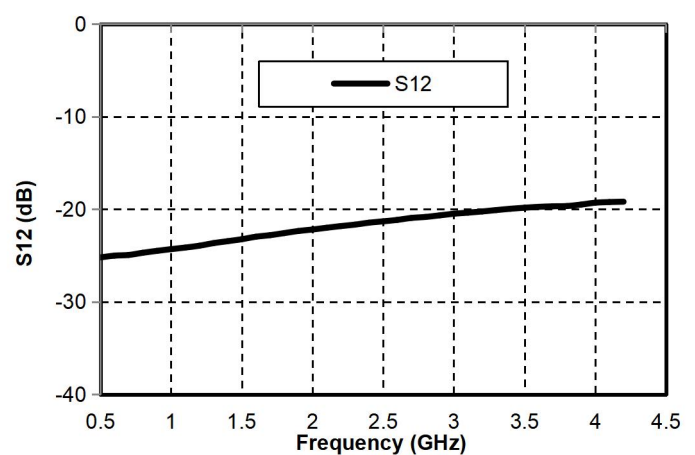
Noise Figure vs. Frequency



Input /Output Return Loss vs. Frequency

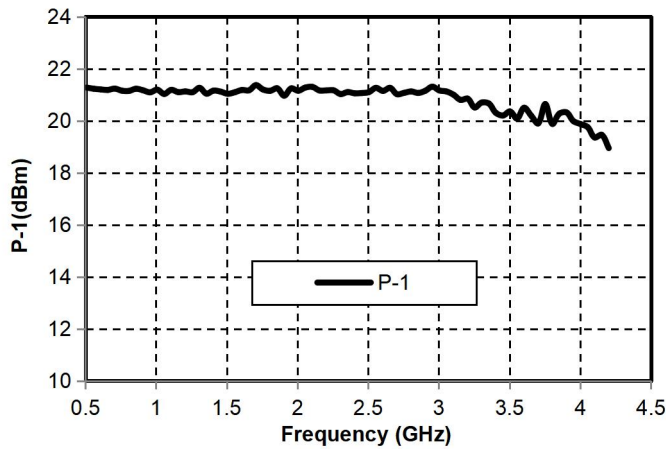


Reverse Isolation vs. Frequency

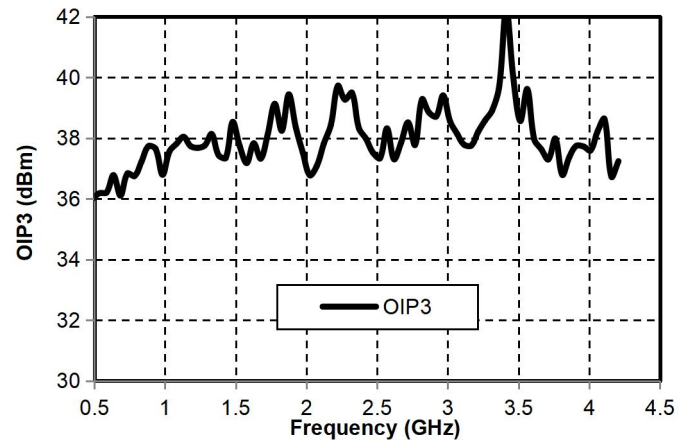


High Linearity Low Noise Gain Amplifier , 50 - 4200 MHz

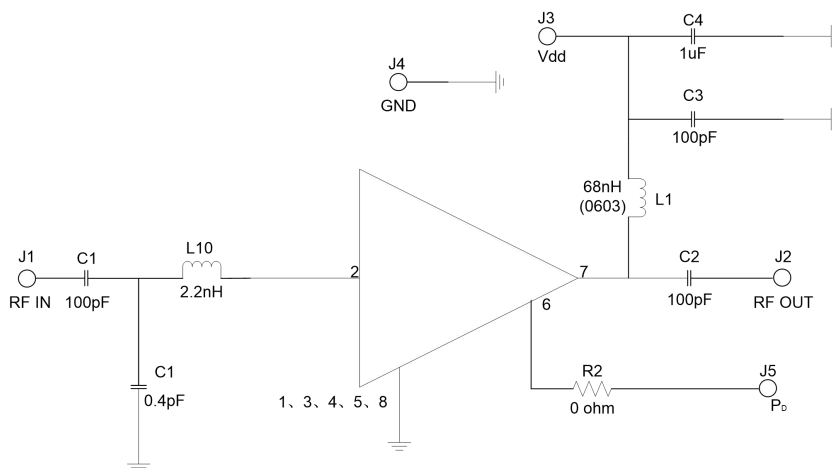
P-1dB vs. Frequency



OIP3 vs. Frequency



500M-4200M recommended circuit diagram



Precautions

- 1、 All resistors and capacitors are packaged in 0402
- 2、 The capacitance values of C1 , C2 and C3 need to be adjusted according to the actual application frequency.
- 3、 The inductance values of L1 and L10 need to be adjusted accordingly according to the actual application frequency.
- 4、 If not needed, R2 can be not installed; when R2 is not installed, the amplifier is always in working condition.

Ingredients list

| Raw material | RC Inductance | Describe | Brand |
|--------------|---------------|------------------------------------|---------|
| R2 | 0 Ω | Resistor, Chip, 0402, 5%, 1/16W | various |
| L1 0 | 2.2 nH | Inductor, 0603, 5%, Ceramic | various |
| L1 | 68nH | Inductor, 0603, 5%, Ceramic | various |
| C4 | 1uF | Cap., Chip, 0402, 10%, 10V, X5R | various |
| C1 C2 C3 | 100 pF | Cap., Chip, 0402, 5%, 50V, NPO/COG | various |

High Linearity Low Noise Gain Amplifier , 50 - 4200 MHz

50M-500M electrical performance parameters

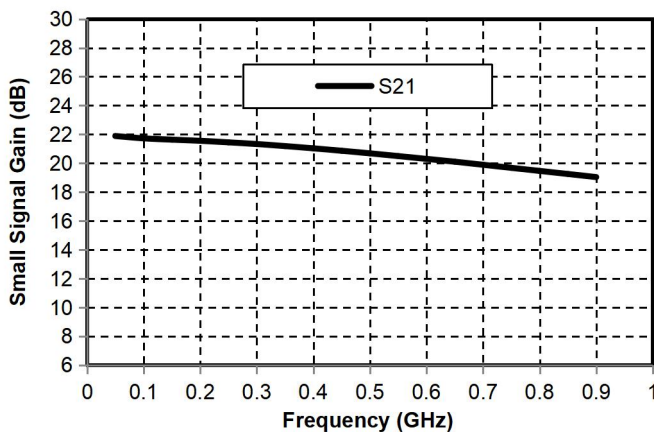
GHLN-9047-DF2-8 can achieve 50-500 MHz intermediate frequency operation by properly adjusting the bias induct value and DC capacitor value .

Electrical performance parameters (TA = +25°C, Vd = +5V, 50Ω system)

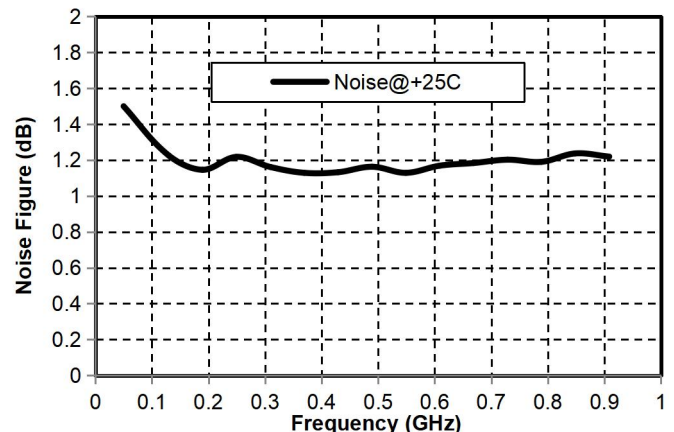
| Index | Test Conditions | Typical Value | | | | Unit |
|--------------------|------------------------------|---------------|------|------|------|------|
| | | 50 | 100 | 200 | 500 | |
| Test frequency | | 50 | 100 | 200 | 500 | MHz |
| Small Signal Gain | | 21.5 | 21.5 | 21.5 | 20.5 | dB |
| Input return loss | | 7.5 | 13.5 | 16 | 15.5 | dB |
| Output return loss | | 12 | 15 | 15 | 15.5 | dB |
| P-1 | | 20 | 20.5 | 20.5 | 20.5 | dBm |
| OIP3 | Pout=+4 dBm /tone, Δf =1 MHz | 33.5 | 34.5 | 34.5 | 35 | dBm |
| Noise Figure* | | 1.5 | 1.3 | 1.2 | 1.2 | dB |

*Noise figure is the test data without de -embedding .

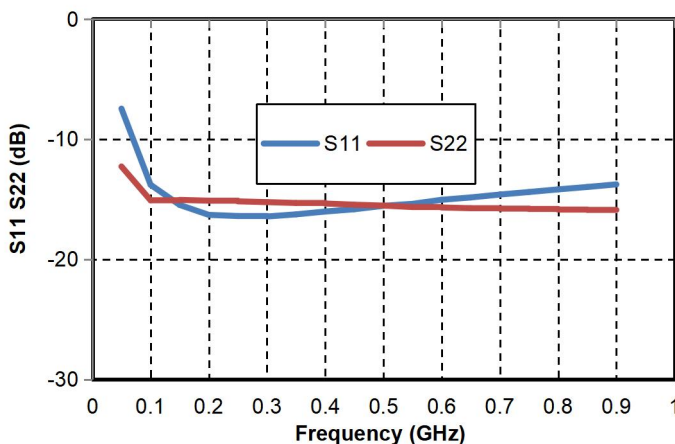
Small Signal Gain vs. Frequency



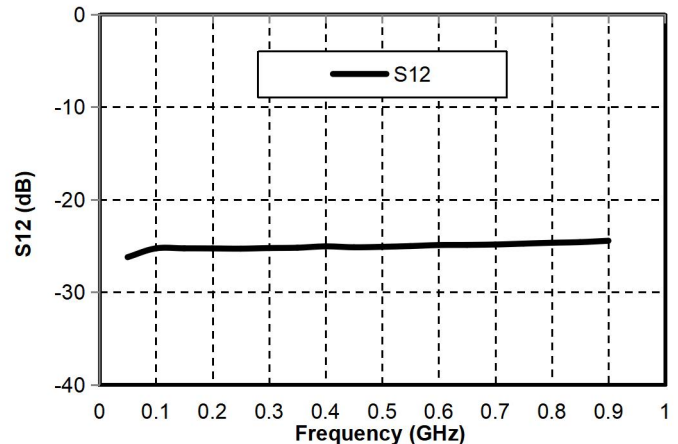
Noise Figure vs. Frequency



Input /Output Return Loss vs. Frequency

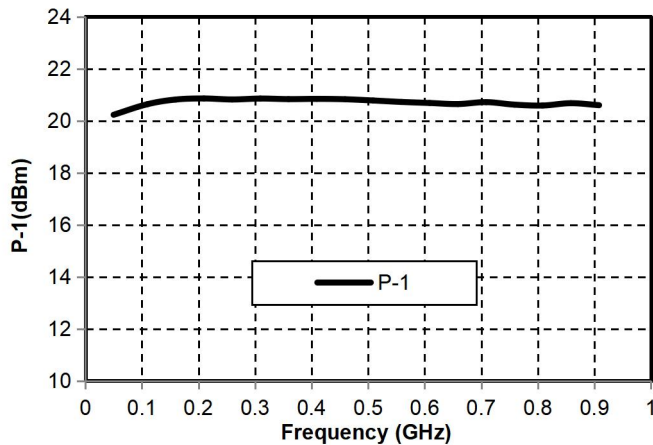


Reverse Isolation vs. Frequency

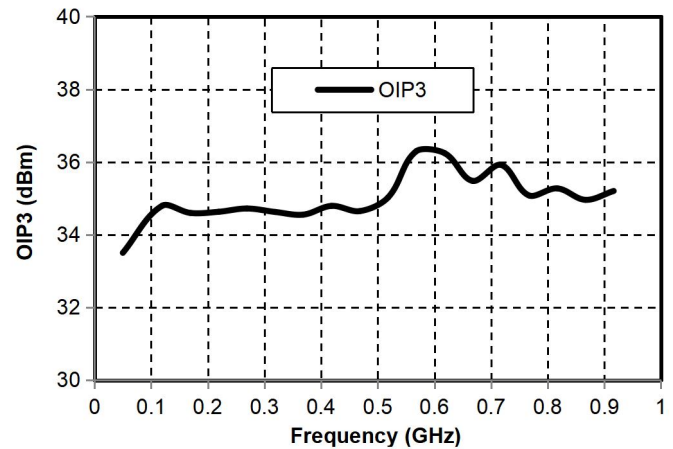


High Linearity Low Noise Gain Amplifier , 50 - 4200 MHz

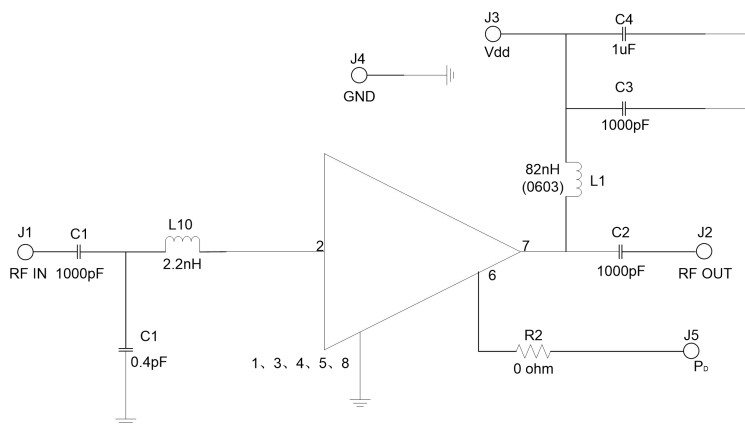
P-1dB vs. Frequency



OIP3 vs. Frequency



50M-500M recommended circuit diagram



Precautions

- 5、 All resistors and capacitors are packaged in 0402
- 6、 The capacitance values of C1 , C2 and C3 need to be adjusted according to the actual application frequency.
- 7、 The inductance values of L1 and L10 need to be adjusted accordingly according to the actual application frequency.
- 8、 If not needed, R2 can be not installed; when R2 is not installed, the amplifier is always in working condition.

Ingredients list

| Raw material | RC Inductance | Describe | Brand |
|--------------|---------------|------------------------------------|---------|
| R2 | 0 Ω | Resistor, Chip, 0402, 5%, 1/16W | various |
| L1 0 | 2.2 nH | Inductor, 0603, 5%, Ceramic | various |
| L1 | 82nH | Inductor, 0603, 5%, Ceramic | various |
| C4 | 1uF | Cap., Chip, 0402, 10%, 10V, X5R | various |
| C1 C2 C3 | 1000 pF | Cap., Chip, 0402, 5%, 50V, NPO/COG | various |

High Linearity Low Noise Gain Amplifier , 50 - 4200 MHz

| Pin Definition | | |
|----------------------|------------------|---|
| Bonding point number | Function Symbol | Functional Description |
| 2 | RF IN | RF input port, impedance 50ohm , requires external DC blocking capacitor |
| 6 | Shut Down | Shutdown control port |
| 7 | RF OUT / DC Bias | RF output port, impedance 50ohm, amplifier leakage bias, bias the circuit at the output end through external current-choking inductor and bias resistor, external DC blocking capacitor is required |
| 1, 3, 4, 5, 8 | NC | No welding required |
| Chip bottom | GND | The bottom of the chip needs to be well grounded to RF and DC |

Use restriction parameter ²

| | |
|--------------------------------------|-----------------------------------|
| Collector voltage: +6V | Input power: +23dBm |
| Operating temperature: -40 ~ +70 ° C | Storage Temperature: -65 ~ +150°C |

【2】 Exceeding any of these maximum limits may cause permanent damage.

Environmental conditions

| parameter | grade | standard |
|----------------------------------|---------|--------------------------|
| ESD – Human Body Model (HBM) | 1A | ESDA / JEDEC JS-001-2014 |
| ESD – Charged Device Model (CDM) | C3 | ESDA / JEDEC JS-001-2014 |
| MSL – Moisture Sensitivity Level | LEVEL 1 | IPC/JEDEC J-STD-020 |

Precautions for use

- Plastic package material : Low-pressure injection molding plastic that meets ROHS specifications
- Lead frame material: copper alloy
- Lead surface plating: 100% matte tin
- Maximum reflow soldering peak temperature: 260°C